

Sus 5-1
contd

a series of conductive traces located on said bottom surface of said base substrate,

B1
end

a plurality of conductive balls connected to said series of conductive traces,

a thin sheet material secured to said base substrate and covering said aperture such that a cavity is formed, said thin sheet material having a thickness of from approximately 0.025 to approximately 0.1 mm, and a semiconductor element mounted in said cavity.

42. (amended) A processor system comprising:

Sus 5-2

a central processing unit; and

B2

a memory device connected to said central processing unit, said memory device comprised of a plurality of low profile ball grid array semiconductor packages, said low profile ball grid array semiconductor packages comprised of a base substrate having a top surface and a bottom surface, said base substrate having an aperture extending from said top surface to said bottom surface,

a series of conductive traces located on said bottom surface of said base substrate,

a plurality of conductive balls connected to said series of conductive traces,

a thin sheet material secured to said top surface of said base substrate and covering said aperture to form a downward facing cavity, said thin sheet material having a thickness of from approximately 0.025 to approximately 0.1 mm, and a semiconductor element mounted in said downward facing cavity.